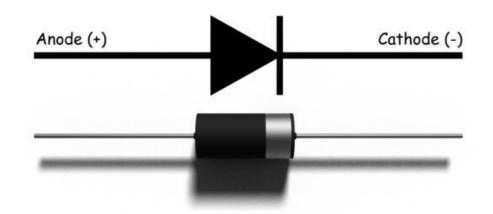
## 電子電路入門導論

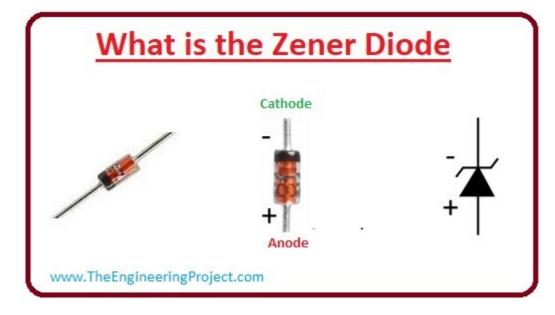
雙極性電晶體-BJT 蘇文鈺 成功大學資訊工程系

本投影片之圖片取自網路

### 二極體 Diode

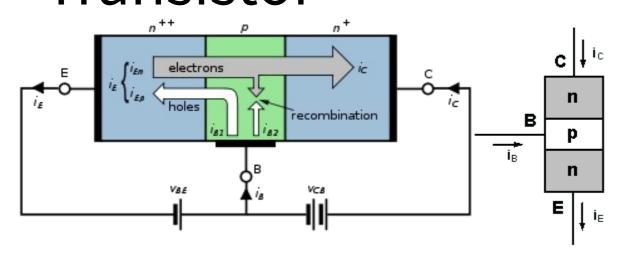


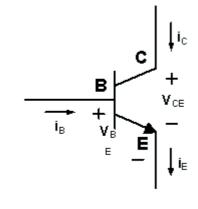
由 P(Anode) 到 N(Cathode) 單向導通

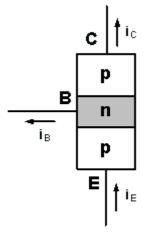


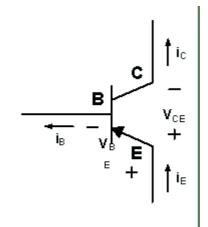
- 由 P(Anode) 到 N(Cathode) 單向導通
- 但是通常反過來用,反向施加電壓時 二極體崩潰後產生固定的導通電壓
  - 可以做為穩壓使用
  - 可以做為參考電壓使用

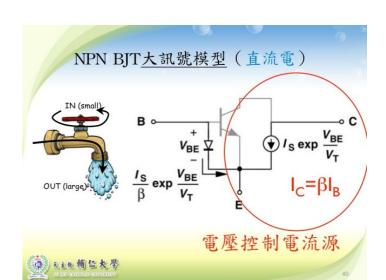
# 雙極性電晶體, Bipolar Junction Transistor











### 性電晶體的規格範例

wicro Commerciai Components

20736 Marilla Street Chatsworth

CA 91311

Phone: (818) 701-4933 Fax: (818) 701-4939

### **Features**

- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Capable of 625mW of Power Disspation and 200mA Ic
- Epoxy meets UL 94 V-0 flammability rating
- Moisure Sensitivity Level 1
- Through Hole Package
- Halogen free available upon request by adding suffix "-HF"
- Operating Temperature: -55°C to +150°C

### • Storage Temperature: -55°C to +150°C Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units		
OFF CHAR	OFF CHARACTERISTICS					
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage* (I <sub>C</sub> =1.0mAdc, I <sub>B</sub> =0)	40		Vdc		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage (I <sub>C</sub> =10μAdc, I <sub>E</sub> =0)	60		Vdc		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>E</sub> =10μAdc, I <sub>C</sub> =0)	6.0		Vdc		
I <sub>BL</sub>	Base Cutoff Current (V <sub>CE</sub> =30Vdc, V <sub>BE</sub> =3.0Vdc)		50	nAdc		
I <sub>CEX</sub>	Collector Cutoff Current (V <sub>CE</sub> =30Vdc, V <sub>BE</sub> =3.0Vdc)		50	nAdc		

ON CHARACTERISTICS

LINUJUH

### **NPN General**

Purpose Amplifier

### ON CHARACTERISTICS

h <sub>FE</sub>	DC Current Gain*			
	$(I_C=0.1 \text{mAdc}, V_{CE}=1.0 \text{Vdc})$	40		
	(I <sub>C</sub> =1.0mAdc, V <sub>CE</sub> =1.0Vdc)	70	8.3.00	
	(I <sub>C</sub> =10mAdc, V <sub>CE</sub> =1.0Vdc)	100	300	
	(I <sub>C</sub> =50mAdc, V <sub>CE</sub> =1.0Vdc)	60		
	(I <sub>C</sub> =100mAdc, V <sub>CE</sub> =1.0Vdc)	30		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage			
	(I <sub>C</sub> =10mAdc, I <sub>B</sub> =1.0mAdc)		0.2	Vdc
	(I <sub>C</sub> =50mAdc, I <sub>B</sub> =5.0mAdc)		0.4	1140001300
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	111111111111111111111111111111111111111	1111111	
	(I <sub>C</sub> =10mAdc, I <sub>B</sub> =1.0mAdc)	0.65	0.85	Vdc
da y	(I <sub>C</sub> =50mAdc, I <sub>B</sub> =5.0mAdc)		0.95	

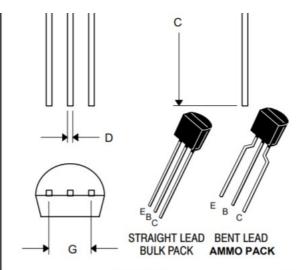
#### **SMALL-SIGNAL CHARACTERISTICS**

f <sub>T</sub>	Current Gain-Bandwidth Product (I <sub>C</sub> =10mAdc, V <sub>CE</sub> =20Vdc, f=100MHz)	250		MHz
C <sub>obo</sub>	Output Capacitance (V <sub>CB</sub> =5.0Vdec, I <sub>E</sub> =0, f=1.0MHz)	Arm	4.0	pF
C <sub>ibo</sub>	Input Capacitance (V <sub>BE</sub> =0.5Vdc, I <sub>C</sub> =0, f=1.0MHz)		8.0	pF
NF	Noise Figure ( $I_C$ =100 $\mu$ Adc, $V_{CE}$ =5.0Vdc, $R_S$ =1.0k $\Omega$ f=10Hz to 15.7kHz)		5.0	dB

#### **SWITCHING CHARACTERISTICS**

$t_d$	Delay Time	(V <sub>CC</sub> =3.0Vdc, V <sub>BE</sub> =0.5Vdc	35	ns
tr	Rise Time	$I_C=10$ mAdc, $I_{B1}=1.0$ mAdc)	35	ns
ts	Storage Time	(V <sub>CC</sub> =3.0Vdc, I <sub>C</sub> =10mAdc	200	ns
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{mAdc}$	50	ns

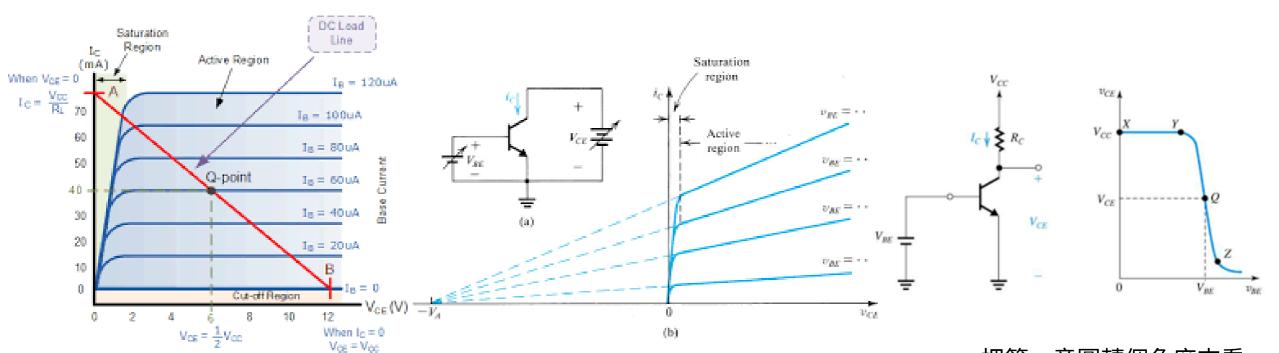
\*Dulas Width - 2000s Duty Cuals - 2 00/



		DIMEN	SIONS		
DIM	INCHES		MM		
	MIN	MAX	MIN	MAX	NOTE
Α	.175	.185	4.45	4.70	2 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
В	.175	.185	4.45	4.70	
C	.500		12.70		
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	Straight Lead
	.173	.220	4.40	5.60	Bent Lead

<sup>\*</sup> For ammo packing detailed specification, click here to visit our website of product packaging for details.

### 特性曲線



較為理想的

稍微誇張一點的,但是比較 可以清楚看出其輸出內部阻抗

把第一章圖轉個角度來看 **Q 為此電晶體的操作點** 

## 偏壓電路 (Biasing)

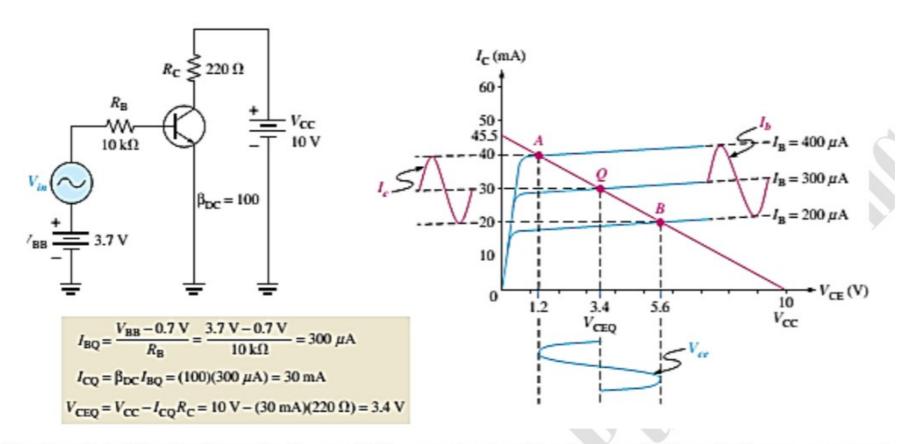
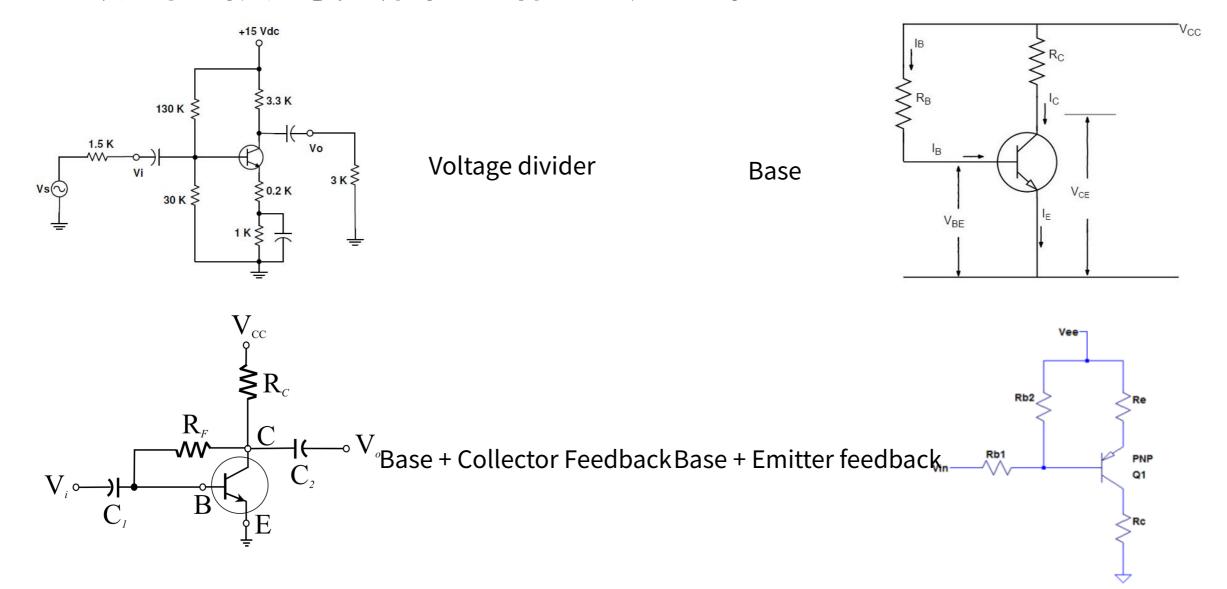
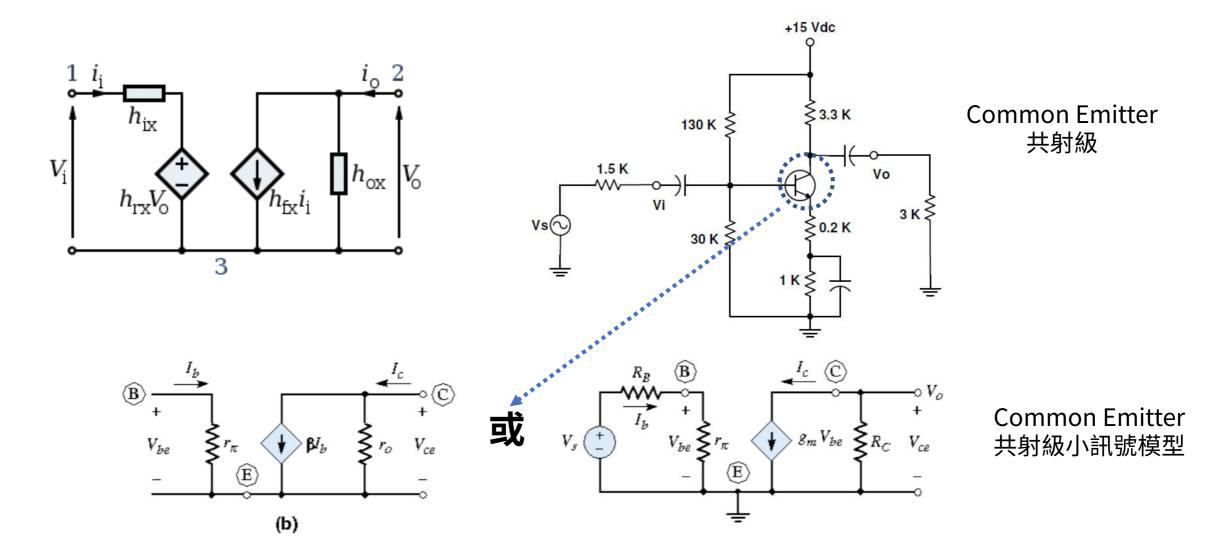


Figure 14: Variations in I<sub>C</sub> and V<sub>CE</sub> as a result of a variation in base current.

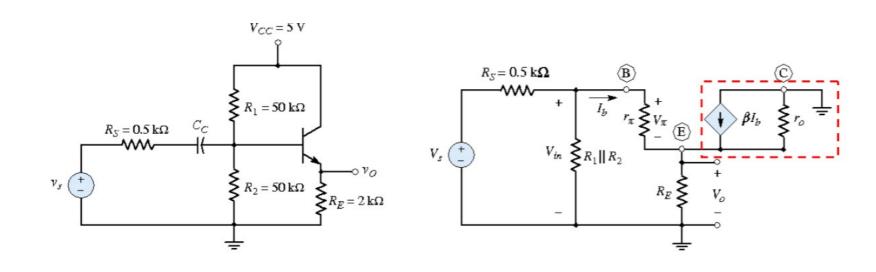
### 幾種較為實際的偏壓方式



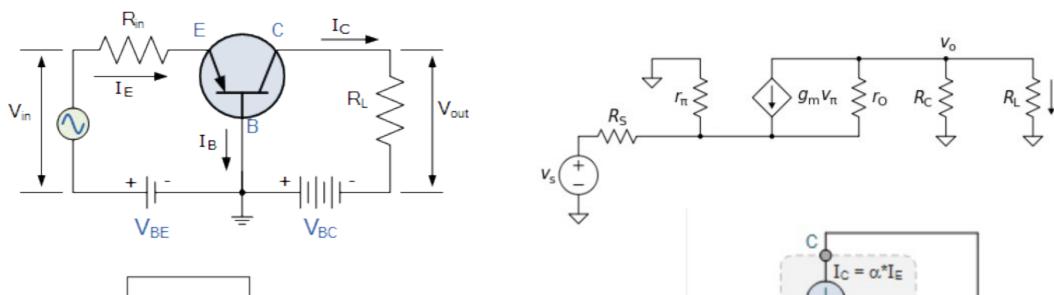
## 小訊號等效模型 (Equivalent Model)

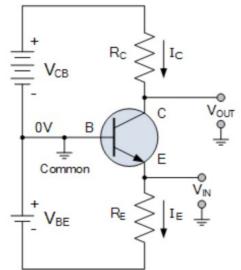


## 共集級 (Common Collector)



## 共基級 (Common Base-amplifier.html





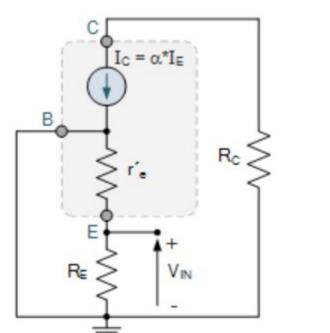
### 電壓放大倍率

= 電流放大倍率 X(Rc/(re||RE))

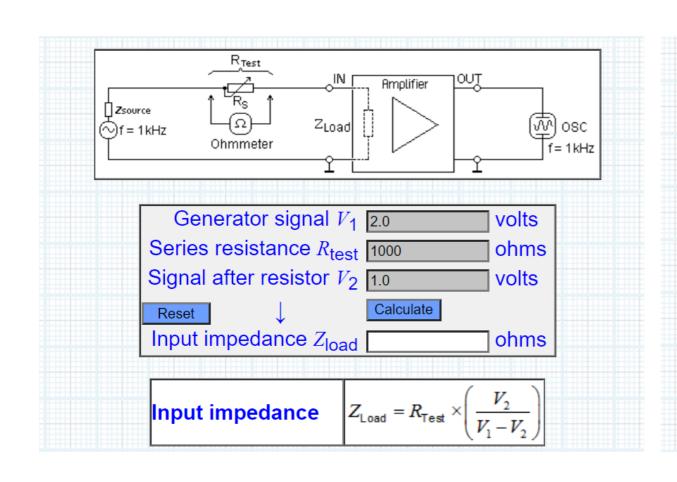
Re 稱為動態內部射級電阻 =.025V/IE

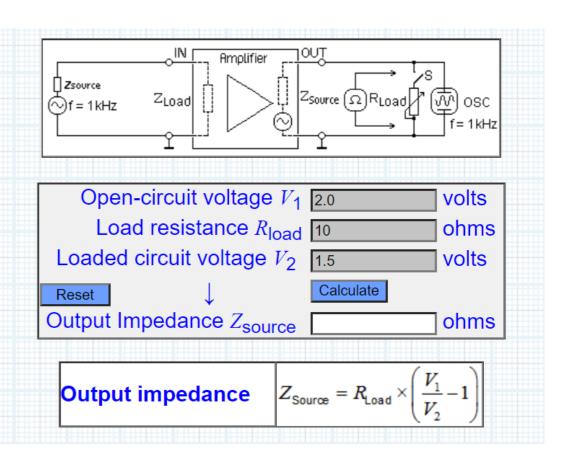
### 特色:

- 1. 因為 re 很小,放大倍率極大
- 2. 輸出阻抗 (Rc) 很大

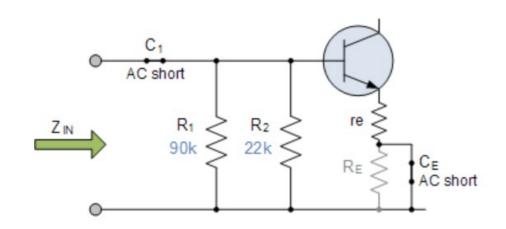


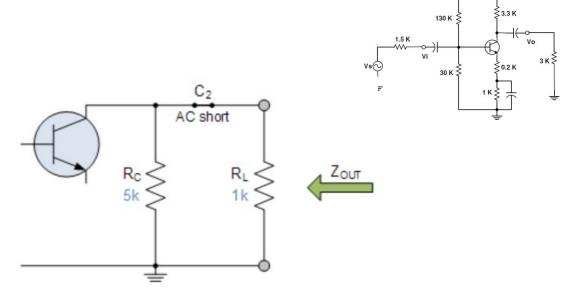
### 輸出與輸入阻抗的測量與計算



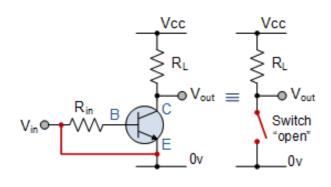


# Common Emitter Input/output impedance

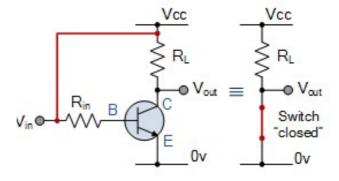




### 電晶體可以當作一個開關使用



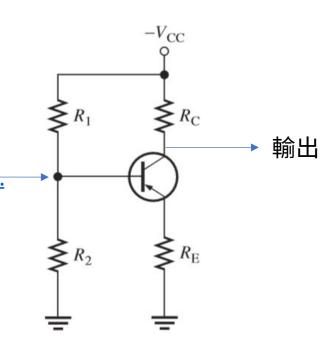
- The input and Base are grounded (Ov)
- Base-Emitter voltage  $V_{BE} < 0.7v$
- Base-Emitter junction is reverse biased
- Base-Collector junction is reverse biased
- Transistor is "fully-OFF" (Cut-off region)
- No Collector current flows (I<sub>C</sub> = 0)
- V<sub>OUT</sub> = V<sub>CE</sub> = V<sub>CC</sub> = "1"
- Transistor operates as an "open switch"



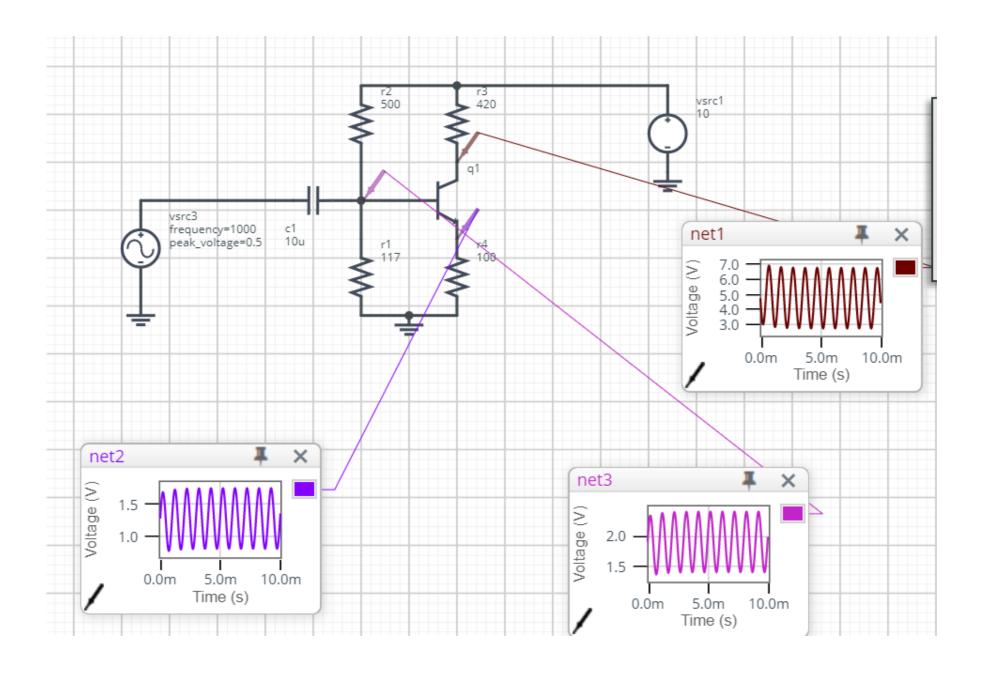
- ullet The input and Base are connected to  $V_{CC}$
- Base-Emitter voltage V<sub>BE</sub> > 0.7v
- Base-Emitter junction is forward biased
- Base-Collector junction is forward biased
- Transistor is "fully-ON" (saturation region)
- Max Collector current flows (I<sub>C</sub> = Vcc/R<sub>L</sub>)
- V<sub>CE</sub> = 0 (ideal saturation)
- V<sub>OUT</sub> = V<sub>CE</sub> = "0"
- Transistor operates as a "closed switch"

## BC337(npn) 與 BC327(pnp)

- •請用 Voltage Divider 的方式,設計一個共射級的放大器。
  - 規格
    - 集級電流為 5~20mA
    - 放大倍率約為 4 倍
    - 輸入電壓 10V
    - BC337 datasheet:
      - <a href="https://www.mouser.tw/datasheet/2/308/BC337-輸入02338">https://www.mouser.tw/datasheet/2/308/BC337-輸入02338</a>.
  - 請問
    - 四個電阻值各為多少?
    - 輸出阻抗為多少?
    - 當輸入訊號為 0 時,集級電壓為幾伏特?
    - 輸入阻抗為幾 Ohm?
    - 在失真極低時,訊號最大擺幅約為幾伏特?



http://www.sengpielaudio.com/calculator-InputOutputImpedance.htm



### Quiz(下周)

- 出題方向
  - BC337 或 BC327
  - 共射極
  - 其他的偏壓方式
  - 電壓仍保持 10V
  - 放大倍率改變
  - 集級電流改變
  - 請計算出前一頁的五個問題

## 實做(下下周)

- •請備妥材料
  - 2N2904 若干顆
  - 可變電阻四個
    - 以你認為適當的數值為準
  - 麵包板一片
    - 請買有附導線者
  - 鱷魚夾連接線兩包
  - 杜邦連接線(公的)
- 驗收
  - 達到 p.11 的要求
  - 測量四個電阻的阻值為多少?
    - 與先前計算出的誤差為多少?

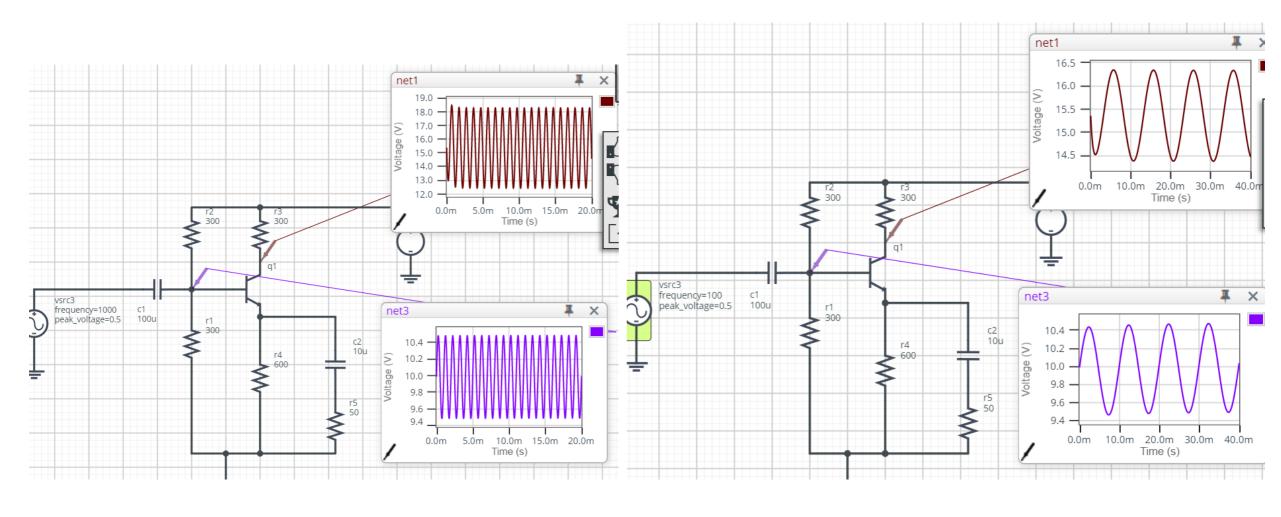
## 測驗 (下下週)

• 基於 Quiz 更為深入的計算問題

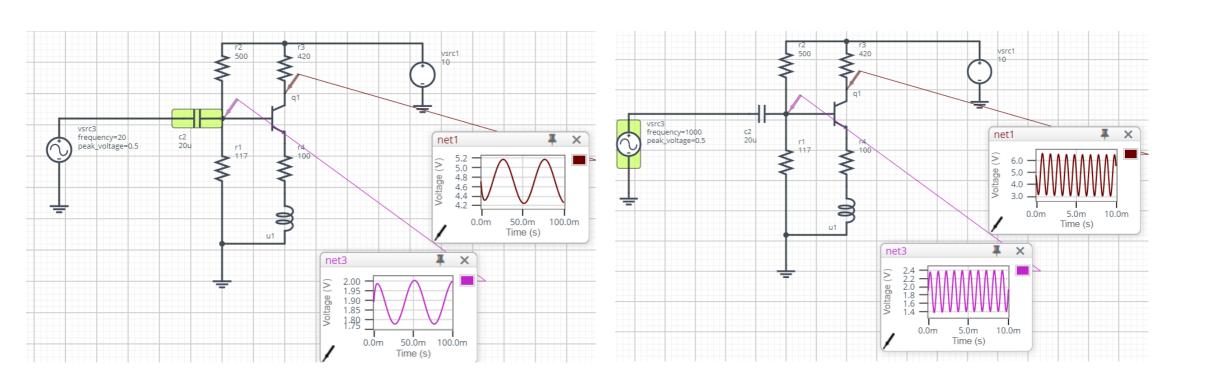
### 實做組準備材料

- BC337 若干顆
- 電阻(依據本周小考所計算的數值,請多準備其他可能會用到的)
- 麵包版
- 三種線材
- 夾子
- 5~10uf 電容兩個

### 如果在射級電阻旁邊加一個電容呢?



### 如果在射級上加一個電感呢?



### 網路參考資料

https://www.electronics-tutorials.ws/amplifier/input-impedance-of-an-amplifier.html

https://www.allaboutcircuits.com/textbook/semiconductors/chpt-4/common-base-amplifier/

https://www.electronics-tutorials.ws/amplifier/input-impedance-of-an-amplifier.html

http://www.industrial-electronics.com/electrnc-dvcs-9e 5.html

https://www.wisc-online.com/learn/career-clusters/stem/sse1302/transistor-fundamentals-voltage-divider-biase

http://www.learningaboutelectronics.com/Articles/Voltage-divider-bias-of-a-BJT-transistor

https://www.electronics-tutorials.ws/amplifier/transistor-biasing.html

https://www.youtube.com/watch?v=zTyuzHokWyA

https://www.youtube.com/watch?v=jQb199oIY5U